

FNK N-Channel Enhancement Mode Power MOSFET

Description

The FNK8606 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .

General Features

 $V_{DS} = 20V, I_{D} = 9A$

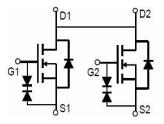
 $R_{DS(ON)} < 16 \,\text{m}\Omega$ @ $V_{GS} = 2.5 V$

 $R_{DS(ON)} < 11 m\Omega @ V_{GS} = 4.5 V$

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- ●PWM application
- Load switch



Schematic diagram



Marking and pin Assignment

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8606	FNK8606	PDFN3*3-8L	Ø180mm	8mm	3000 units

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _G s	±12	V	
Drain Current-Continuous	I _D	9	Α	
Drain Current-Pulsed (Note 1)	I _{DM}	35	Α	
Maximum Power Dissipation	P _D	1.5	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	83.3	°C/W
--	----------------	------	------

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μΑ

FNK-Semiconductor 1/7 Rev.1.1



Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm10V, V_{DS}=0V$	-	-	±10	μΑ
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =5A	-	9.1	11	mΩ
Diam-Source On-State Resistance		V _{GS} =2.5V, I _D =5A	-	11.5	16	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =7A	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ =10\/\/ =0\/	-	2100	-	PF
Output Capacitance	C _{oss}	V_{DS} =10V, V_{GS} =0V, F=1.0MHz	-	250	-	PF
Reverse Transfer Capacitance	C _{rss}	1 – 1.0IVII IZ	-	220	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	6		nS
Turn-on Rise Time	t _r	V_{DD} =10V,R _L =1.35 Ω	-	13		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =5V, R_{GEN} =3 Ω	-	52		nS
Turn-Off Fall Time	t _f		-	16		nS
Total Gate Charge	Qg	\/ -10\/ -74	-	15		nC
Gate-Source Charge	Q_{gs}	$V_{DS}=10V,I_{D}=7A,$ $V_{GS}=4.5V$	-	0.8	-	nC
Gate-Drain Charge	Q_{gd}	VGS-4.5V	-	3.2	-	nC
Drain-Source Diode Characteristics				•		
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	7	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

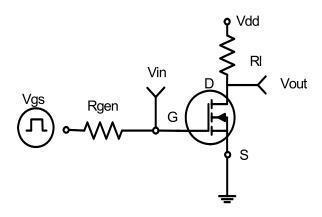


Figure 1:Switching Test Circuit

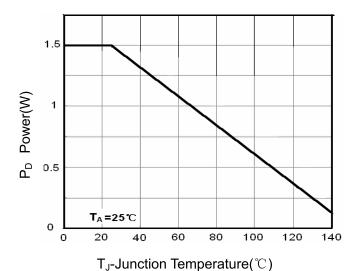


Figure 3 Power Dissipation

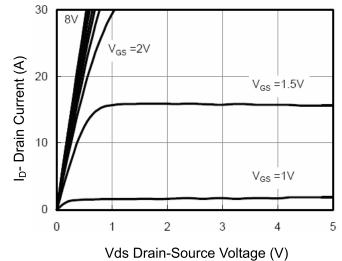


Figure 5 Output CHARACTERISTICS

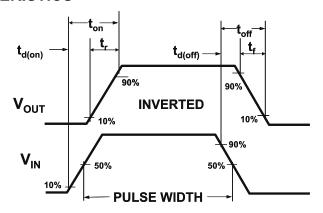


Figure 2:Switching Waveforms

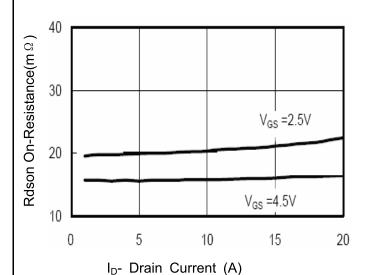


Figure 6 Drain-Source On-Resistance

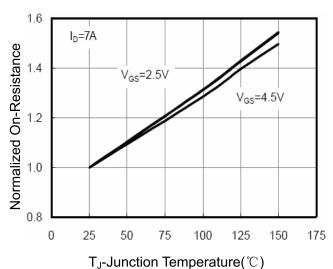
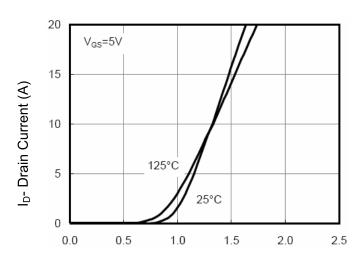


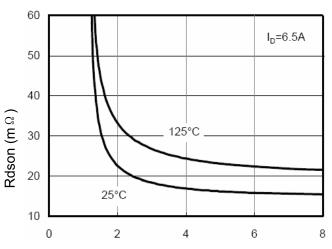
Figure 8 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)





Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

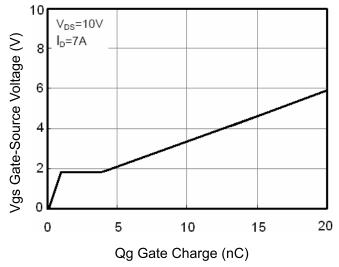
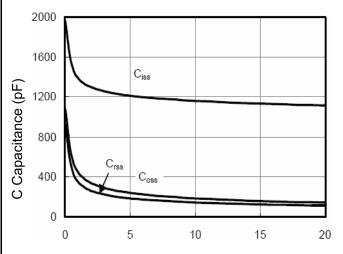
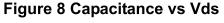


Figure 11 Gate Charge



Vds Drain-Source Voltage (V)



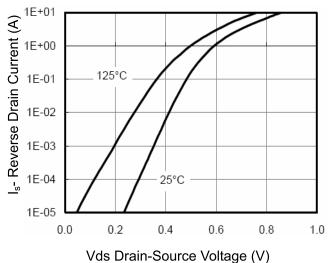


Figure 10 Capacitance vs Vds

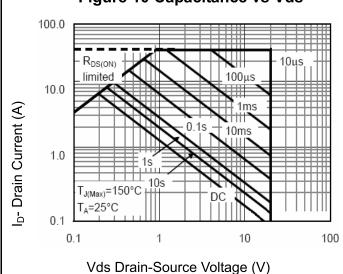


Figure 13 Safe Operation Area



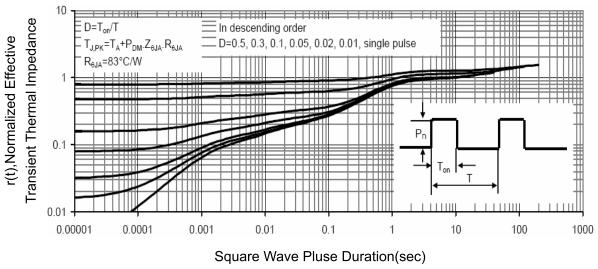
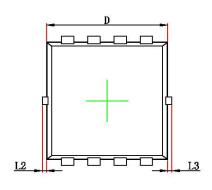


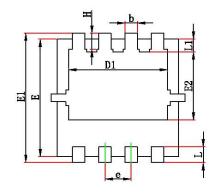
Figure 14 Normalized Maximum Transient Thermal Impedance

FNK-Semiconductor 5/7 Rev.1.1



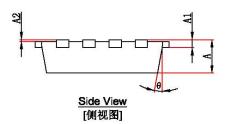
PDFNWB(3 × 3)-8L(P0.65T0.80) PACKAGE OUTLINE DIMENSIONS





Top View [顶视图]

Bottom View [背视图]



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.650	0.850	0.026	0.033	
A1	0.152	REF.	0.006 REF.		
A2	0~0).05	0~0	.002	
D	2.900	3.100	0.114	0.122	
D1	2.300	2.600	0.091	0.102	
E	2.900	3.100	0.114	0.122	
E1	3.150	3.450	0.124	0.136	
E2	1.535	1.935	0.060	0.076	
b	0.200	0.400	0.008	0.016	
е	0.550	0.750	0.022	0.030	
L	0.300	0.500	0.012	0.020	
L1	0.180	0.480	0.007	0.019	
L2	0~0	.100	0~0	.004	
L3	0~0.100		0~0.004		
Н	0.315	0.515	0.012	0.020	
θ	9°	13°	9°	13°	



ATTENTION:

- FNK reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- FNK assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all FNK products described or contained herein.
- Specifications of any and all FNK products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- FNKstrives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all FNK products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the FNK product that you intend to use.
- FNK will supply the best possible product for customers!

FNK-Semiconductor 7/7 Rev.1.1